

9/24/03

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2272	SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Leonard Forbes		
				FILING DATE Filed Herewith	GROUP Unknown	
U.S. PATENT DOCUMENTS						
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<div style="font-size: 2em; margin: 0;">LP</div> <div style="font-size: 2em; margin: 0;">I</div> <div style="font-size: 2em; margin: 0;">V</div>	AA	4,241,359	12/23/1980	Izumi et al		
	AB	5,441,591	08/15/1995	Forbes		
	AC	6,049,106	04/11/2000	Forbes		
	AD	5,234,535	08/10/1993	Beyer et al		
	AE	6,093,623	07/25/2000	Forbes		
	AF	6,309,950	10/30/2001	Forbes		
	AG					
	AH					
	AI					
	AJ					
	AK					
	AL					
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation Yes No
	AM					
	AN					
	AO					
	AP					
	AQ					
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
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EXAMINER			DATE CONSIDERED			
<div style="font-size: 1.5em; margin: 0;">Long Pham</div>			<div style="font-size: 1.5em; margin: 0;">4/14/05</div>			
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U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
LP	AA	10/443,335	Forbes			05/21/2003	
	AB						
	AC						
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	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AM						
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	AO						
	AP						
	AQ						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-2272	SERIAL NO. Filed Herewith
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				FILING DATE Filed Herewith	GROUP Unknown
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
LP	AA	S.S.K. Iyer et al., "Separation by Plasma Implantation of Oxygen (SPIMOX) operational phase space," IEEE trans. On Plasma Science, Vol. 25, No.3, pp. 1128-135, 1997			
	AB	G.A. Garcia et al, High Quality in Thin (100nm) Silicon on Sapphire," IEEE Trans Electron Devices vol. no. 9, no. 1, pp. 32-34, Jan. (1988)			
	AC	E. Cartagena, G. Garcia, G. Imthurn, G. Kelley, H. Walker and L. Forbes, "Bonded Etchback Silicon on Sapphire Bipolar Junction Transistors," Abstracts of ECS meeting, May 1993, Honolulu, Hawaii, P. 1199.			
	AD	G.P. Imthurn, G.A. Garcia, H.W. Walker, and L. Forbes, "Bonded Silicon-On-Sapphire Wafers and Devices", J. Appl. Phys., 72(6), 15 September 1992, pp. 2526-2527			
	AE	P. Ball, "A Small Mountain of Materials Goes into Every Microchip," Nature Science Update, 19 Nov. 2002, http://www.nature.com/nsu/21028/021028-12.html			
	AF	"Materials Selector", Reinhold Publishing Co., Penton/IPC. http://www.handyharmancanada.com/TheBrazingBook/comparis.htm			
	AG	Company page http://www.hithermaln.com/datasheets/index.cfm?page=values			
	AH	R. People et al, "Calculation of Critical Layer Thickness Versus Lattice Mismatch for Ge ₂ Si ₃ /Si Strained Layer Heterostructures," Appl. Phys. Letters, Vol. 47, P. 322-324, August 1985.			
	AI	R. People et al, "Erratum: Calculation of Critical Layer Thickness Versus Lattice Mismatch for Ge ₂ Si ₃ /Si Strained Layer Heterostructures," Appl. Phys. Letters, Vol. 49, P. 229, July 1986.			
	AJ	G. Grenet et al., "Testing the Feasibility of Strain Relaxed Compliant Substrates," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, P.8.			
	AK	K.D. Hobart et al, "High Ge-Content Relaxed Si ₃ Ge ₂ Layers by Relaxation on Compliant Substrate with Controlled Oxidation," Abstract of Electronic Materials Conferences, Santa Barbara, June 2002, pp. 8.			
	AL	P. Moran et al., "Strain Relaxation in Wafer-bonded SiGe/Si Heterostructures Due to the Viscous Flow of an Underlying Borosilicate Glass," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, pp. 8-9			
	AM	A.J. Auberton-Herve, "SOI: Materials to Systems," Digest of the International Electron Device Meeting, San Francisco, December 1996, pp. 5-10			
	AN	T. Tsuchida et al., "Self-combustion Reaction Induced by Mechanical Activation of Al-ni-c Powder Mixtures," European Journal of Solid State and Inorganic Chemistry (France), Vol. 32, No. 7-8, pp. 629-38, 1995.			
	AO	H.C. Yi, et al, "Combustion Synthesis of Aluminoborate Glass Matrices," J. Mater. Synth. Process. (USA), Vol. 8, No. 1, pp. 15-20, Jan. 2000.			
	AP	Dip.-Ing. M. Wild, Dr.-Ing. A. Gullner, "Laser Assisted Bonding of Silicon and Glass in Micro-System Technology," http://www.ilt.fhg.de/eng/jb00-s42.html			
✓	AQ	Suman Dharmatilake et al, "Anodic Bonding of Glass to Glass and Silicon to Glass or Silicon to Silicon Through a Very Thick Thermally Grown SiO ₂ Layer," Proceedings of IS 34 International Symposium on Smart Structures & Microsystems, Hong Kong, October 19-21, 2000, p. 32. http://dolphin.eng.us.edu/projects/bonding/paper.pdf			
	AR				
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	AU				
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